

2SK1429-VB Datasheet

N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY

| | |
|--|--------|
| V_{DS} (V) | 100 |
| $R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V | 0.036 |
| I_D (A) ^a | 55 |
| Configuration | Single |

FEATURES

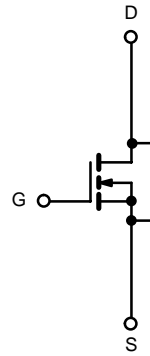
- Trench Power MOSFETS
- 175 °C Junction Temperature
- Low Thermal Resistance Package


RoHS*
 COMPLIANT

TO-220AB



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

| Parameter | Symbol | Limit | Unit |
|--|----------------|------------------|------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current ($T_J = 175$ °C) | I_D | 55 | A |
| | | 40 | |
| Pulsed Drain Current | I_{DM} | 135 | |
| Avalanche Current | I_{AR} | 35 | |
| Repetitive Avalanche Energy ^a | E_{AR} | 61 | mJ |
| Maximum Power Dissipation ^a | P_D | 127 ^b | W |
| | | 3.75 | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 175 | °C |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Limit | Unit |
|--------------------------|------------|-------|------|
| Junction-to-Ambient | R_{thJA} | 40 | °C/W |
| Junction-to-Case (Drain) | R_{thJC} | 1.4 | |

Notes:

a. Duty cycle ≤ 1 %.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).

* Pb containing terminations are not RoHS compliant, exemptions may apply.

| SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted | | | | | | |
|--|---------------|--|------|-------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{SS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$ | 100 | | | V |
| Gate-Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 1 | | 3 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$ | | | 50 | |
| | | $V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 175\text{ }^{\circ}\text{C}$ | | | 250 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$ | 75 | | | A |
| Drain-Source On-State Resistance ^a | $r_{DS(on)}$ | $V_{GS} = 10\text{ V}$, $I_D = 5\text{ A}$ | | 0.036 | | Ω |
| | | $V_{GS} = 4.5\text{ V}$, $I_D = 3\text{ A}$ | | 0.038 | | |
| | | $V_{GS} = 10\text{ V}$, $I_D = 5\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$ | | 0.050 | | |
| | | $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $T_J = 175\text{ }^{\circ}\text{C}$ | | 0.065 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}$, $I_D = 15\text{ A}$ | 10 | | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$ | | 4500 | | pF |
| Output Capacitance | C_{oss} | | | 270 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 90 | | |
| Total Gate Charge ^c | Q_g | $V_{DS} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$ | | 35 | 60 | nC |
| Gate-Source Charge ^c | Q_{gs} | | | 11 | | |
| Gate-Drain Charge ^c | Q_{gd} | | | 9 | | |
| Gate Resistance | R_G | | | 1.7 | | Ω |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = 50\text{ V}$, $R_L = 1.25\text{ }\Omega$ $I_D \cong 40\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_G = 2.5\text{ }\Omega$ | | 11 | 20 | ns |
| Rise Time ^c | t_r | | | 12 | 20 | |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | | | 30 | 45 | |
| Fall Time ^c | t_f | | | 12 | 20 | |
| Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^{\circ}\text{C}$ ^b | | | | | | |
| Continuous Current | I_S | | | | 40 | A |
| Pulsed Current | I_{SM} | | | | 120 | |
| Forward Voltage ^a | V_{SD} | $I_F = 30\text{ A}$, $V_{GS} = 0\text{ V}$ | | 1.0 | 1.5 | V |
| Reverse Recovery Time | t_{rr} | $I_F = 30\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ | | 60 | 100 | ns |
| Peak Reverse Recovery Current | $I_{RM(REC)}$ | | | 5 | 8 | A |
| Reverse Recovery Charge | Q_{rr} | | | | 0.15 | 0.4 |

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

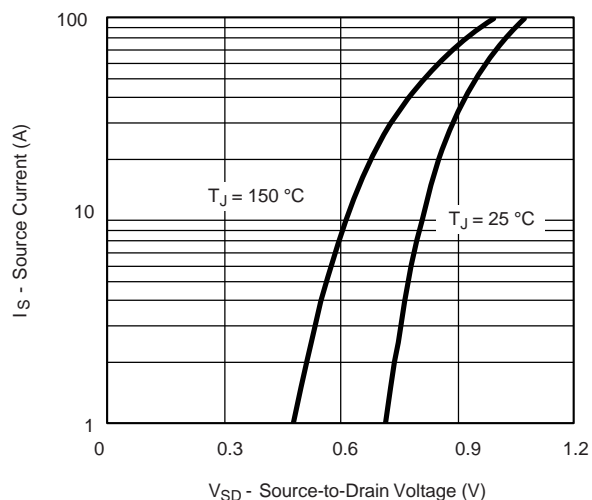
Transconductance

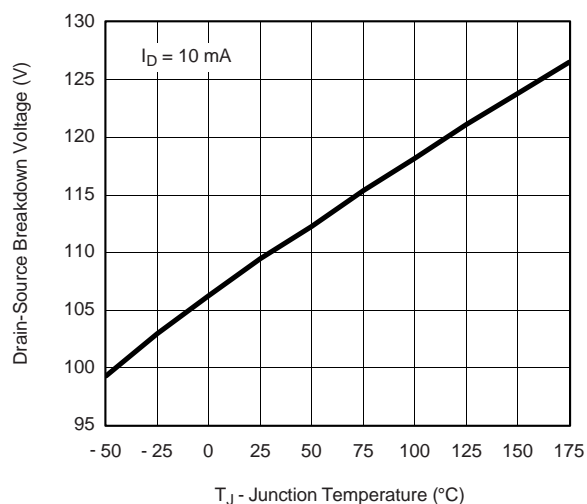
On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

Avalanche Current vs. Time

Drain-Source Breakdown Voltage vs. Junction Temperature

THERMAL RATINGS



**Maximum Avalanche and Drain Current
vs. Case Temperature**



* $V_{GS} > \text{minimum } V_{GS} \text{ at which } r_{DS(on)} \text{ is specified}$

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-220AB



| DIM. | MILLIMETERS | | INCHES | |
|-----------------|-------------|-------|--------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.25 | 4.65 | 0.167 | 0.183 |
| b | 0.69 | 1.01 | 0.027 | 0.040 |
| b(1) | 1.20 | 1.73 | 0.047 | 0.068 |
| c | 0.36 | 0.61 | 0.014 | 0.024 |
| D | 14.85 | 15.49 | 0.585 | 0.610 |
| E | 10.04 | 10.51 | 0.395 | 0.414 |
| e | 2.41 | 2.67 | 0.095 | 0.105 |
| e(1) | 4.88 | 5.28 | 0.192 | 0.208 |
| F | 1.14 | 1.40 | 0.045 | 0.055 |
| H(1) | 6.09 | 6.48 | 0.240 | 0.255 |
| J(1) | 2.41 | 2.92 | 0.095 | 0.115 |
| L | 13.35 | 14.02 | 0.526 | 0.552 |
| L(1) | 3.32 | 3.82 | 0.131 | 0.150 |
| $\varnothing P$ | 3.54 | 3.94 | 0.139 | 0.155 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |

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DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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